

P-Channel Enhancement Mode MOSFET

1. Product Information

Features

- Advanced trench technology
- Excellent $R_{DS(ON)}$
- Low gate charge

Applications

- Battery protection
- Load switch
- Uninterruptible power supply

Quick reference

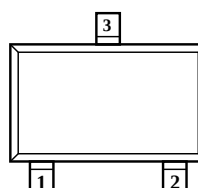
- $V_{DS} \geq -60V$
- $I_D \leq -3.8A$
- $R_{DS(ON)} \leq 150m\Omega @ V_{GS} = -10V$ (Type: 125m Ω)

Pin Description

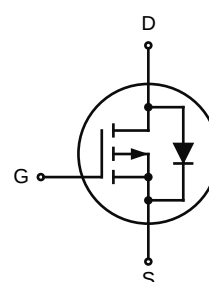
Pin	Description
1	Gate(G)
2	Source(S)
3	Drain(D)

Simplified Outline

Symbol



SOT-23-3L
Top View



Package Marking and Ordering Information

Product Name	Package	Marking	Reel Size	Tape width	Quantity
KJ3P06S	SOT-23-3L	W3P6 YWWXXX: Date Code			3000

2. Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_{D@T_A=25^{\circ}C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.8	A
$I_{D@T_A=70^{\circ}C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-2.4	A
I_{DM}	Pulsed Drain Current ²	-12	A
$P_{D@T_A=25^{\circ}C}$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	$^{\circ}C/W$

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-60	-67	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.021	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-1.5A	---	125	150	mΩ
		V _{GS} =-4.5V, I _D =-1A	---	158	200	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	1.7	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.08	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-1.5A	---	5.9	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-1.5A	---	4.6	---	nC
Q _{gs}	Gate-Source Charge		---	1.4	---	
Q _{gd}	Gate-Drain Charge		---	1.62	---	
T _{d(on)}	Turn-On Delay Time	V _{DS} =-15V, V _{GS} =-10V, R _G =3.3Ω, I _D =-1A	---	17.4	---	ns
T _r	Rise Time		---	5.4	---	
T _{d(off)}	Turn-Off Delay Time		---	37.2	---	
T _f	Fall Time		---	2.4	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	531	---	pF
C _{oss}	Output Capacitance		---	59	---	
C _{rss}	Reverse Transfer Capacitance		---	38	---	
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-1.7	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-7	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

4. Typical Characteristics

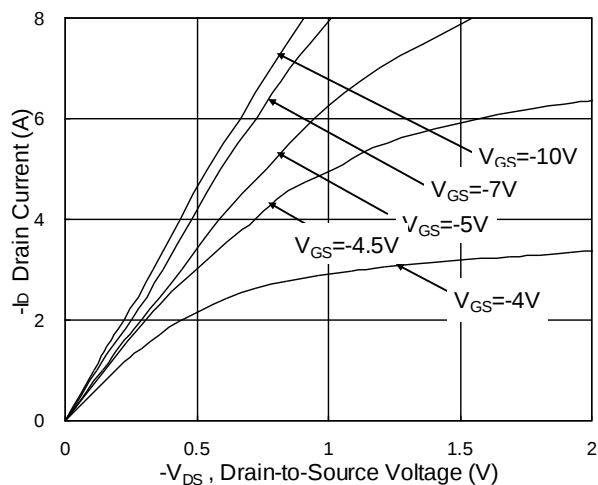


Fig.1 Typical Output Characteristics

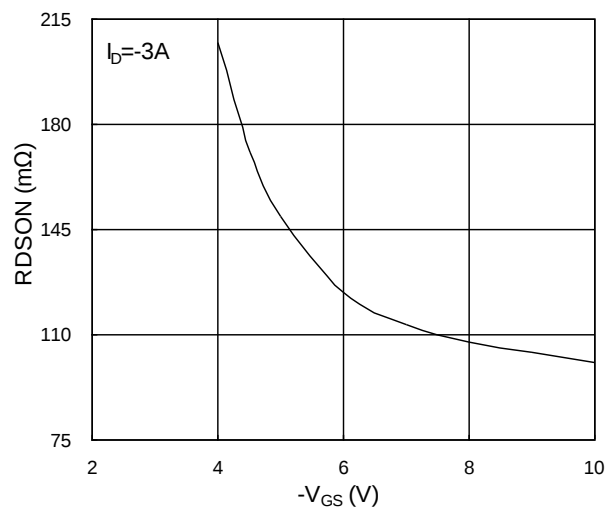


Fig.2 On-Resistance vs. G-S Voltage

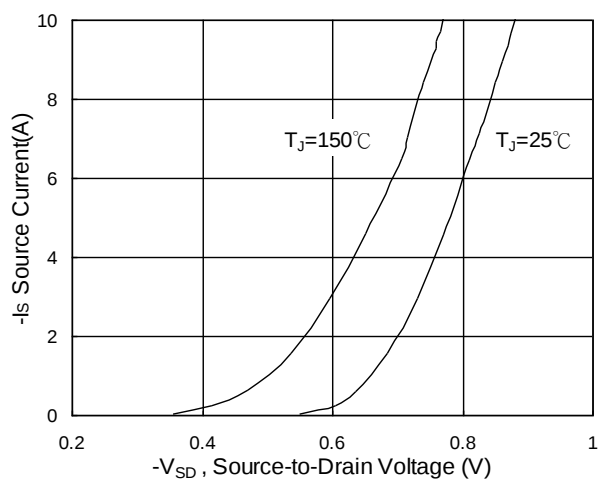


Fig.3 Forward Characteristics Of Reverse

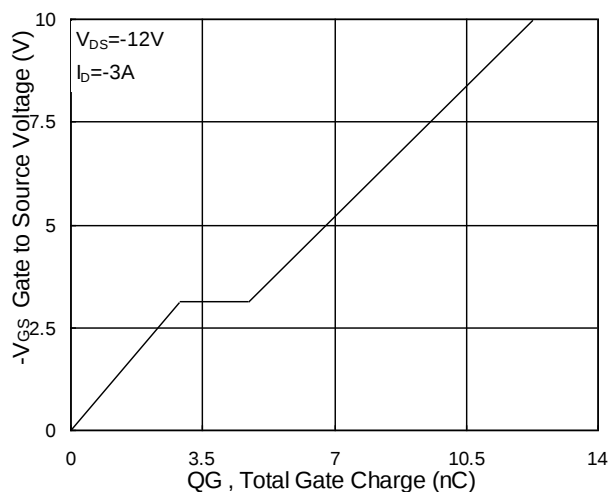


Fig.4 Gate-Charge Characteristics

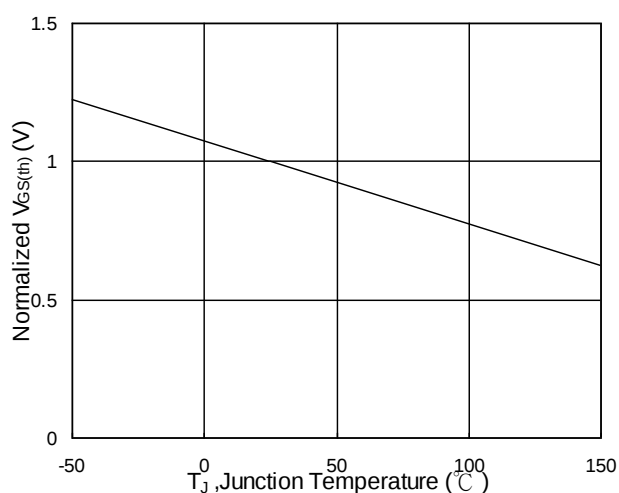


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

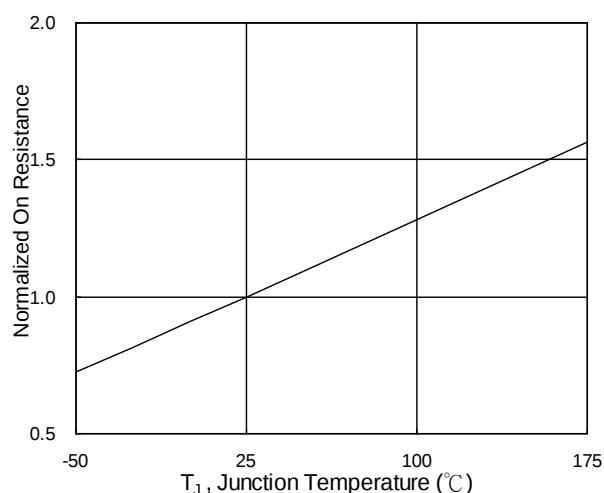


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

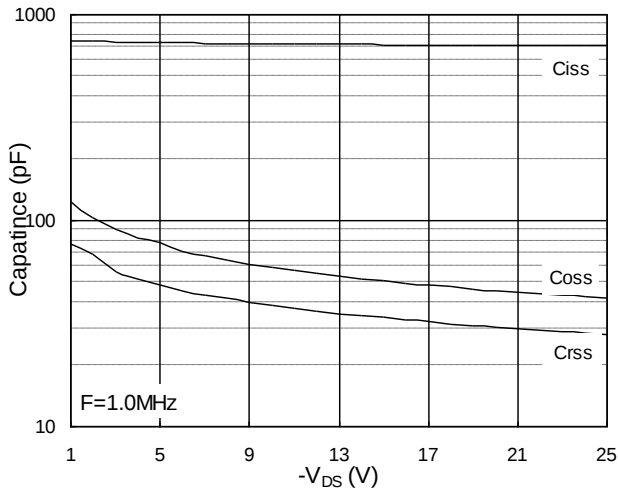


Fig.7 Capacitance

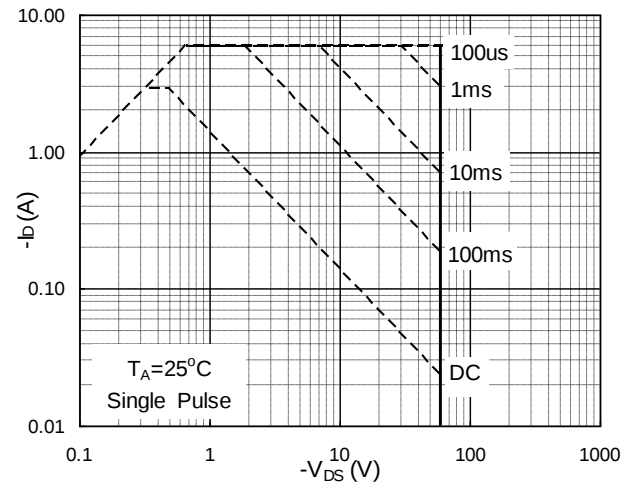


Fig.8 Safe Operating Area

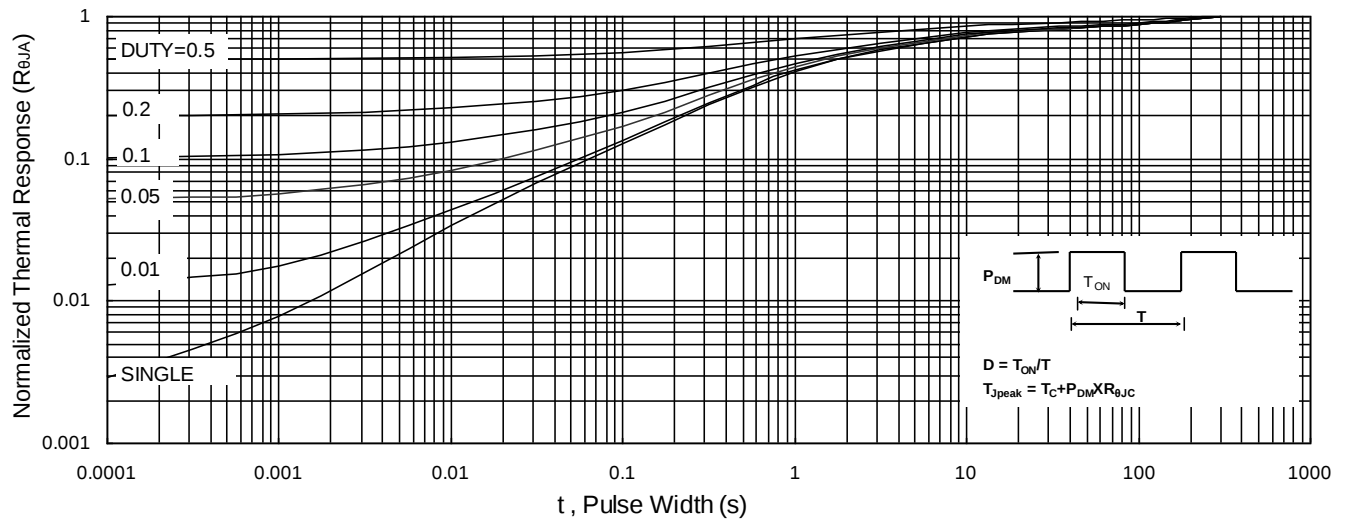


Fig.9 Normalized Maximum Transient Thermal Impedance

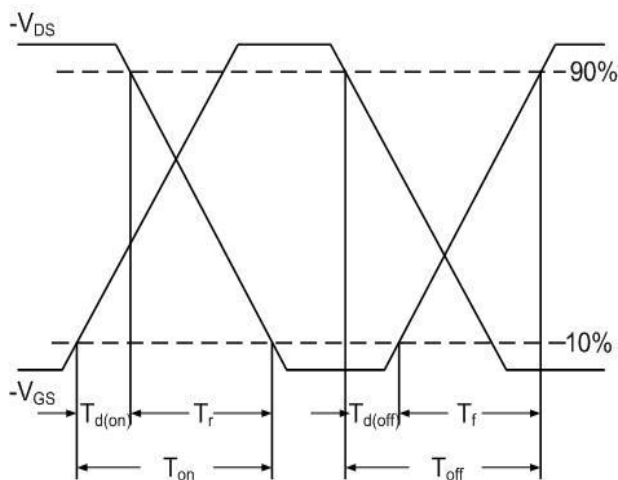


Fig.10 Switching Time Waveform

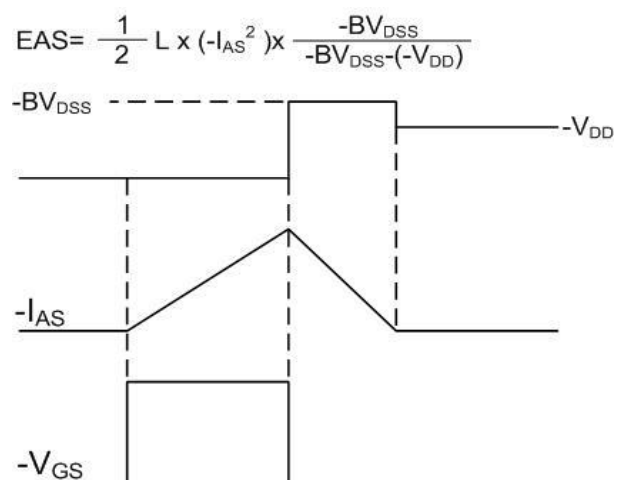
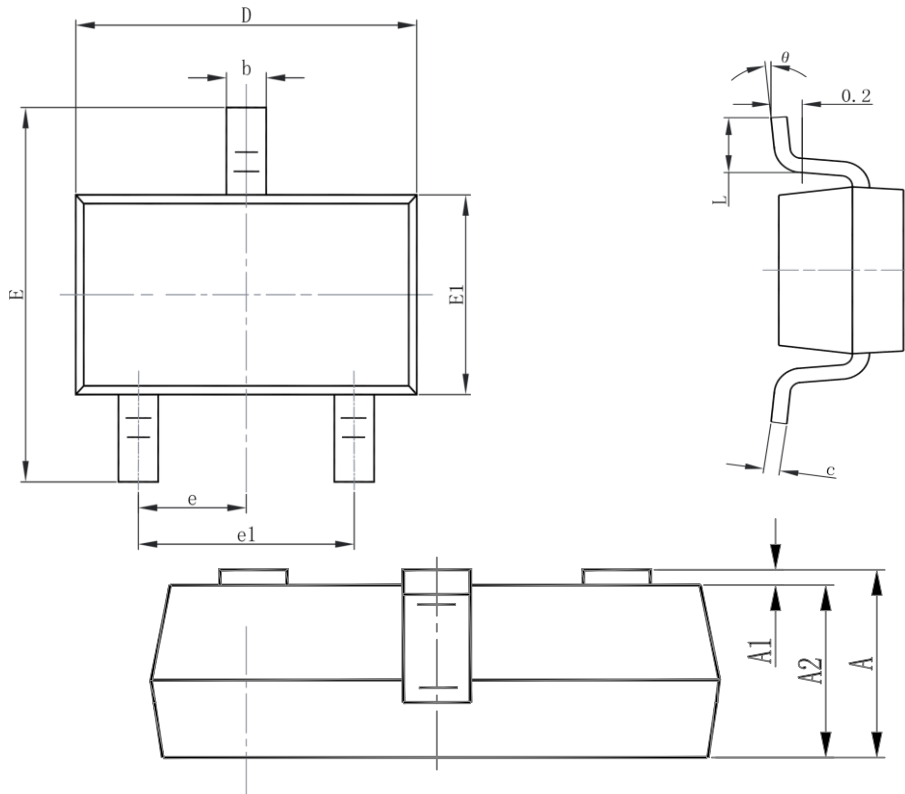


Fig.11 Unclamped Inductive Waveform

5.Package Mechanical Data

SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°